Preliminary datasheet
62 mm C-Series module with CoolSiC™ Trench MOSFET

Features

- Electrical features
  - V_{DSS} = 1200 V
  - I_{DN} = 420 A / I_{DRM} = 840 A
  - High current density
  - Low switching losses
- Mechanical features
  - 4 kV AC 1 min insulation

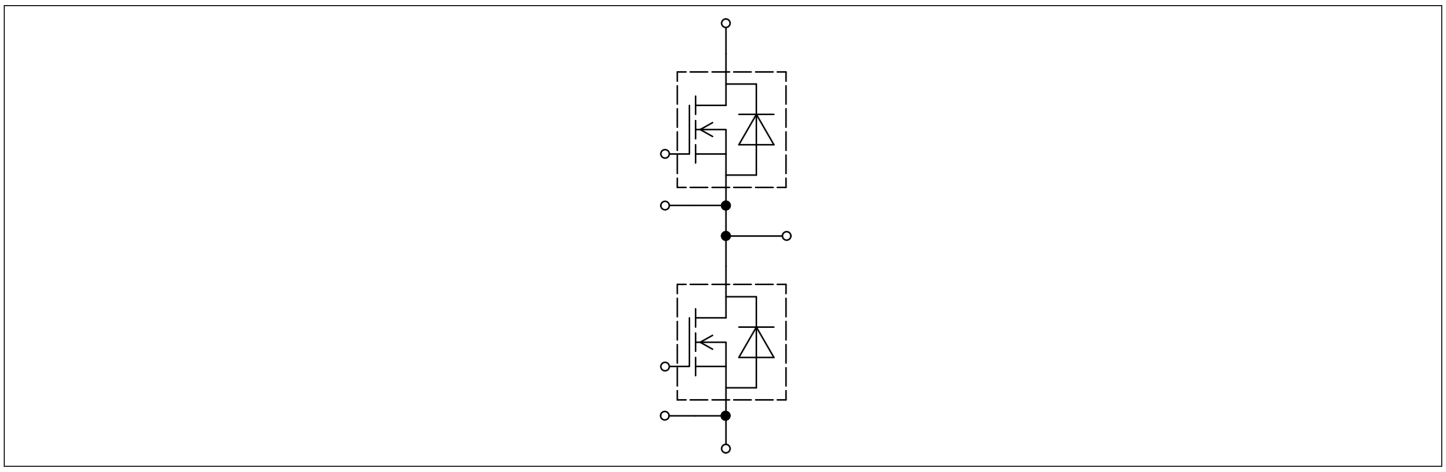
Potential applications

- UPS systems
- Solar applications
- DC/DC converter
- High-frequency switching application
- Energy storage systems
- DC charger for EV

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description



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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, *t* = 60 s	4.0	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	29.0	mm
Creepage distance	d_{Creep}	terminal to terminal	23.0	mm
Clearance	d_{Clear}	terminal to heatsink	23.0	mm
Clearance	d_{Clear}	terminal to terminal	11.0	mm
Comparative tracking index	*CTI*		> 400	
Relative thermal index (electrical)	*RTI*	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Stray inductance module	L_{sCE}				20		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	T_C = 25 °C, per switch			0.475		mΩ
Storage temperature	T_{stg}			-40		125	°C
Mounting torque for module mounting	*M*	- Mounting according to valid application note	M6, Screw	3		6	Nm
Terminal connection torque	*M*	- Mounting according to valid application note	M6, Screw	2.5		5	Nm
Weight	*G*				340		g

2 MOSFET

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		T_{vj} = 25 °C	1200	V
Implemented drain current	I_{DN}			420	A
Continuous DC drain current	I_{DDC}	T_{vj} = 175 °C, V_{GS} = 18 V	T_C = 115 °C	290	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}		840	A

(table continues...)

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Gate-source voltage, max. transient voltage	V_{GS}	$D < 0.01$	-10/23	V
Gate-source voltage, max. static voltage	V_{GS}		-7/20	V

Table 4 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	I_D = 420 A	V_{GS} = 18 V, T_{vj} = 25 °C		1.96		mΩ
			V_{GS} = 18 V, T_{vj} = 125 °C		3.17		
			V_{GS} = 18 V, T_{vj} = 175 °C		4.21		
			V_{GS} = 15 V, T_{vj} = 25 °C		2.36		
Gate threshold voltage	$V_{GS(th)}$	I_D = 168 mA, V_{DS} = V_{GS}, T_{vj} = 25 °C, (tested after 1ms pulse at V_{GS} = +20 V)		3.45	4.3	5.15	V
Total gate charge	Q_G	V_{DD} = 800 V, V_{GS} = -3/18 V			1.2		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			1.3		Ω
Input capacitance	C_{ISS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		36.3		nF
Output capacitance	C_{OSS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		1.8		nF
Reverse transfer capacitance	C_{rss}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.118		nF
C_{OSS} stored energy	E_{OSS}	V_{DS} = 800 V, V_{GS} = -3/18 V, T_{vj} = 25 °C			709		µJ
Drain-source leakage current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = -3 V	T_{vj} = 25 °C		0.24	527	µA
Gate-source leakage current	I_{GSS}	V_{DS} = 0 V, T_{vj} = 25 °C	V_{GS} = 20 V			400	nA

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-on delay time (inductive load)	$t_{d\,on}$	I_D = 420 A, R_{Gon} = 4.7 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V	T_{vj} = 25 °C		143		ns
			T_{vj} = 125 °C		132		
			T_{vj} = 175 °C		130		
Rise time (inductive load)	t_r	I_D = 420 A, R_{Gon} = 4.7 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V	T_{vj} = 25 °C		153		ns
			T_{vj} = 125 °C		142		
			T_{vj} = 175 °C		127		
Turn-off delay time (inductive load)	$t_{d\,off}$	I_D = 420 A, R_{Goff} = 1.5 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V	T_{vj} = 25 °C		150		ns
			T_{vj} = 125 °C		162		
			T_{vj} = 175 °C		169		
Fall time (inductive load)	t_f	I_D = 420 A, R_{Goff} = 1.5 Ω, V_{DD} = 600 V, V_{GS} = -3/18 V	T_{vj} = 25 °C		33		ns
			T_{vj} = 125 °C		33		
			T_{vj} = 175 °C		34		
Turn-on energy loss per pulse	E_{on}	I_D = 420 A, V_{DD} = 600 V, L_σ = 10 nH, V_{GS} = -3/18 V, R_{Gon} = 4.7 Ω, di/dt = 5.2 kA/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		17.2		mJ
			T_{vj} = 125 °C		16.8		
			T_{vj} = 175 °C		17.2		
Turn-off energy loss per pulse	E_{off}	I_D = 420 A, V_{DD} = 600 V, L_σ = 10 nH, V_{GS} = -3/18 V, R_{Goff} = 1.5 Ω, dv/dt = 14.2 kV/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		7.5		mJ
			T_{vj} = 125 °C		8		
			T_{vj} = 175 °C		8.4		
Thermal resistance, junction to case	R_{thJC}	per MOSFET				0.113	K/W
Thermal resistance, case to heat sink	R_{thCH}	per MOSFET, λ_{grease} = 1 W/(m·K)			0.0320		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

Note: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2021-13 must be considered to ensure sound operation of the device over the planned lifetime.

Tvj,op > 150°C is allowed for operation at overload conditions for MOSFET and body diode. For detailed specifications, please refer to AN 2021-13.

3 Body diode (MOSFET)

Table 6 Maximum rated values

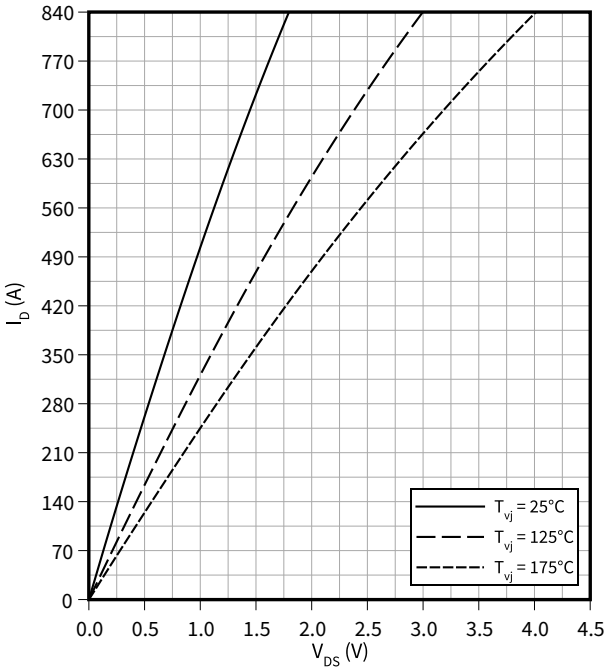
Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	I_{SD}	T_{vj} = 175 °C, V_{GS} = -3 V	T_C = 115 °C	135	A

Table 7 Characteristic values

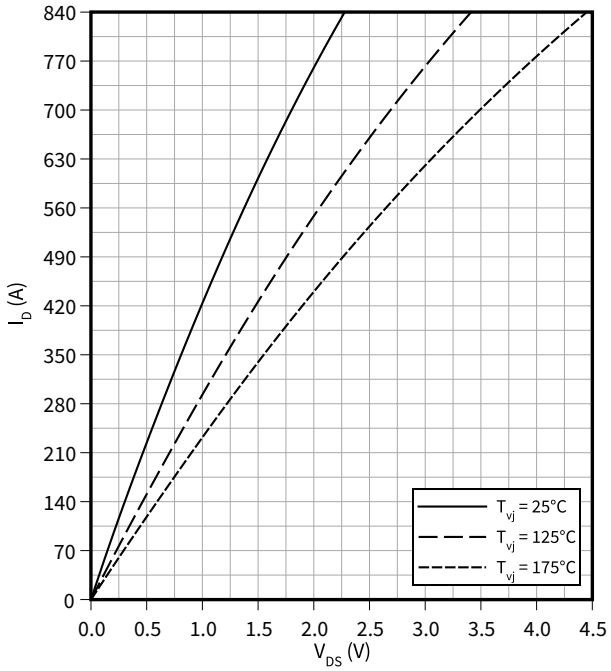
Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_{SD}	I_{SD} = 420 A, V_{GS} = -3 V	T_{vj} = 25 °C		4.22	5.59	V
			T_{vj} = 125 °C		3.95		
			T_{vj} = 175 °C		3.85		

4 Characteristics diagrams

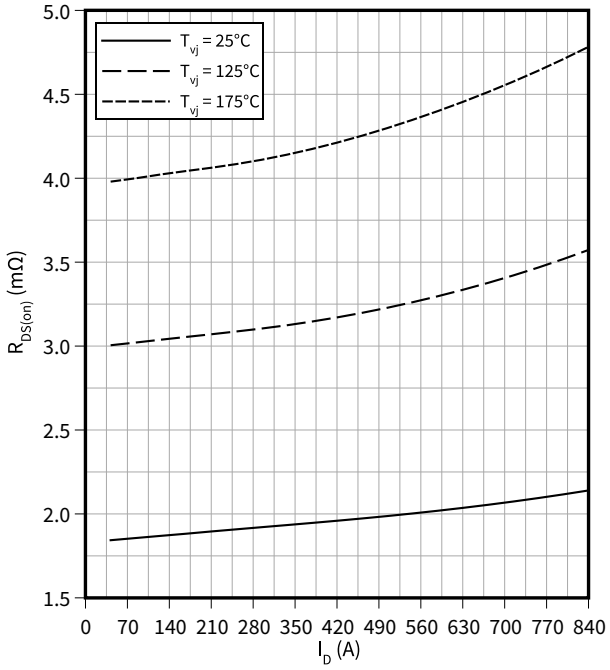
Output characteristic (typical), MOSFET
$I_D = f(V_{DS})$
$V_{GS} = 18$ V



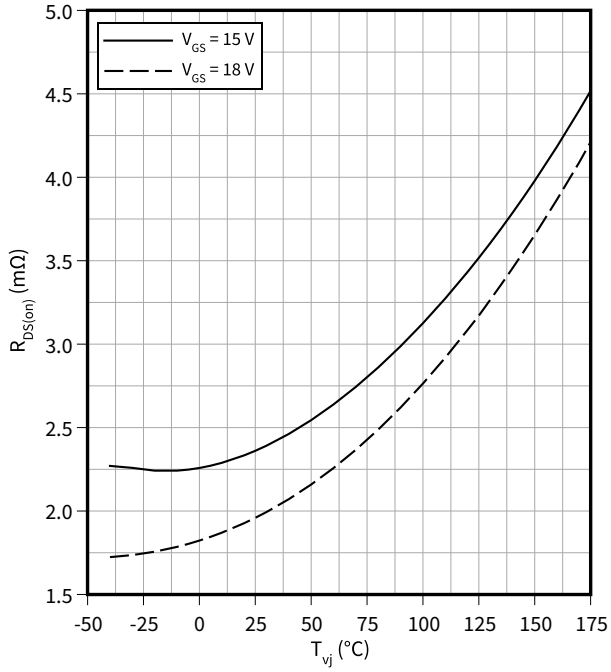
Output characteristic (typical), MOSFET
$I_D = f(V_{DS})$
$V_{GS} = 15$ V



Drain source on-resistance (typical), MOSFET
$R_{DS(on)} = f(I_D)$
$V_{GS} = 18$ V

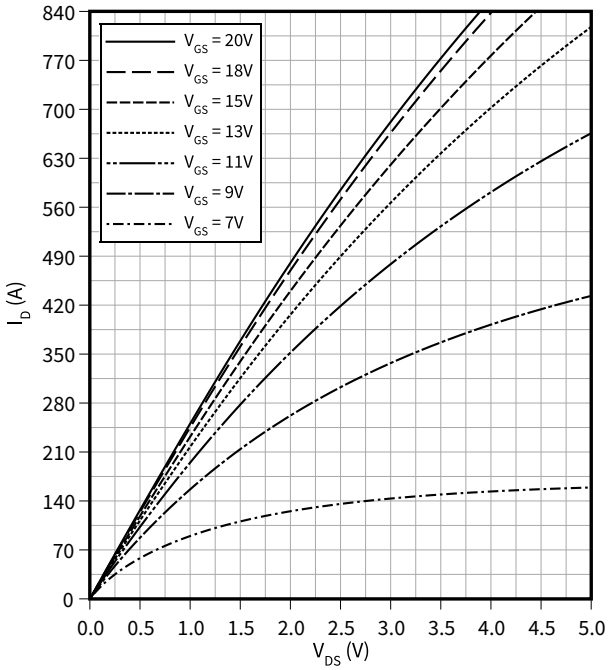


Drain source on-resistance (typical), MOSFET
$R_{DS(on)} = f(T_{vj})$
$I_D = 420$ A



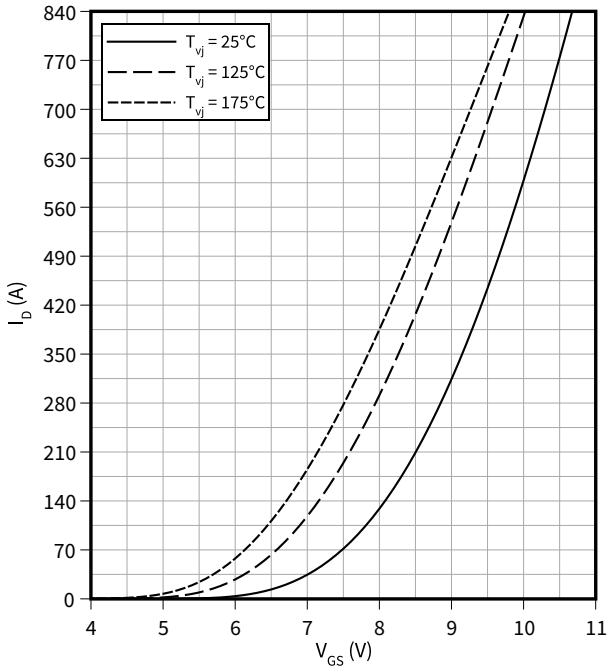
Output characteristic field (typical), MOSFET

$I_D = f(V_{DS})$
$T_{vj} = 175\ °C$



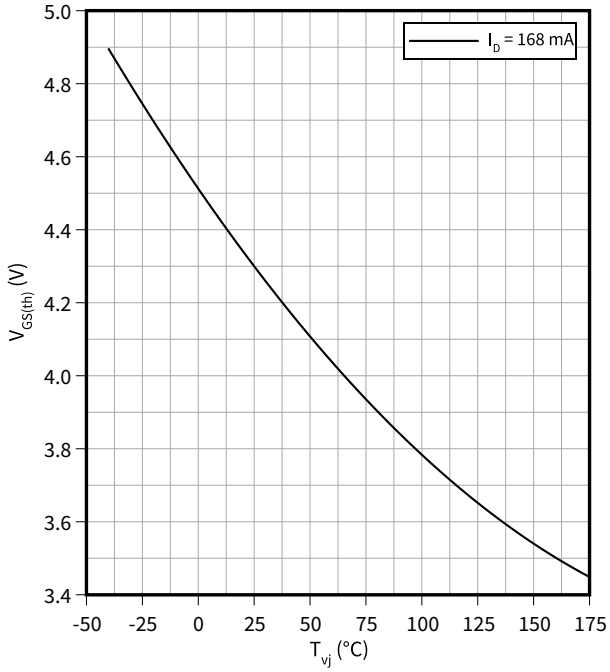
Transfer characteristic (typical), MOSFET

$I_D = f(V_{GS})$
$V_{DS} = 20\ V$



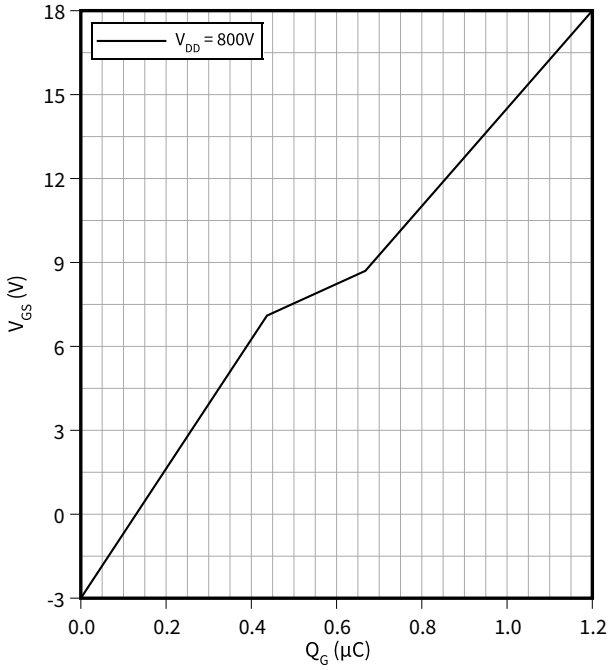
Gate-source threshold voltage (typical), MOSFET

$V_{GS(th)} = f(T_{vj})$
$V_{GS} = V_{DS}$



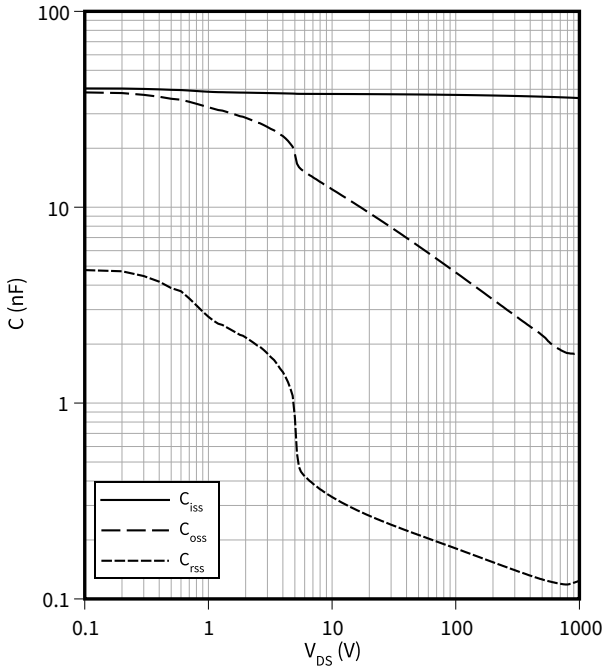
Gate charge characteristic (typical), MOSFET

$V_{GS} = f(Q_G)$
$I_D = 420\ A,\ T_{vj} = 25\ °C$



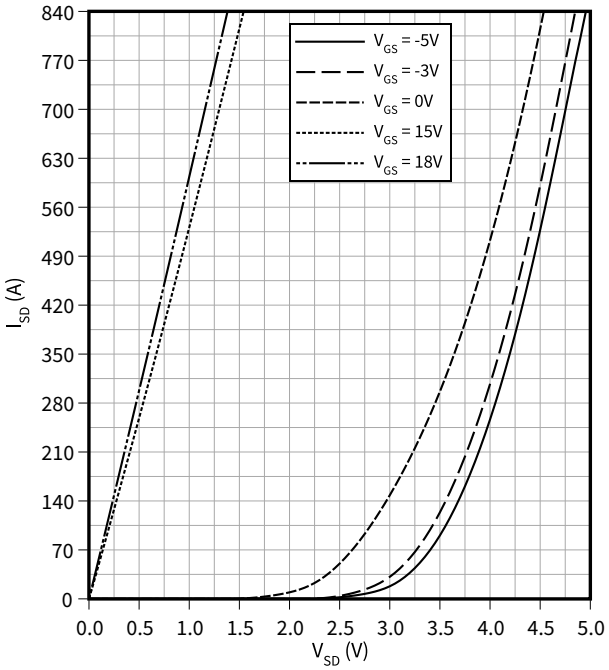
Capacity characteristic (typical), MOSFET

$C = f(V_{DS})$
$f = 100\ kHz$, $T_{vj} = 25\ °C$, $V_{GS} = 0\ V$



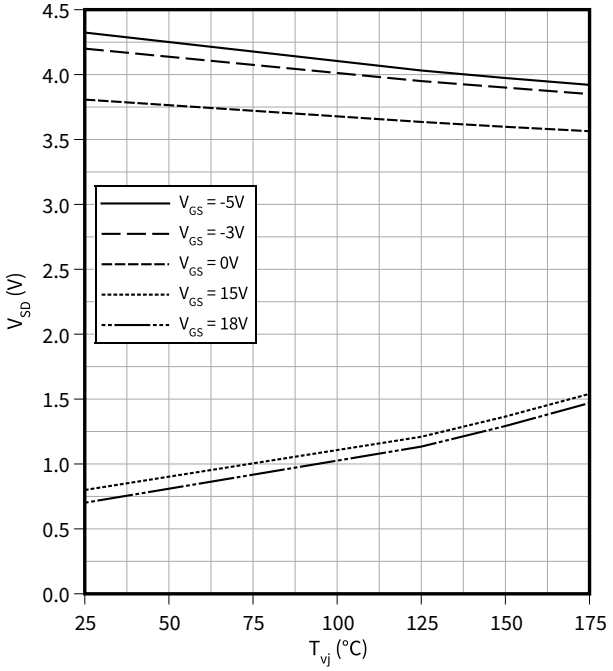
Forward characteristic body diode (typical), MOSFET

$I_{SD} = f(V_{SD})$
$T_{vj} = 25\ °C$



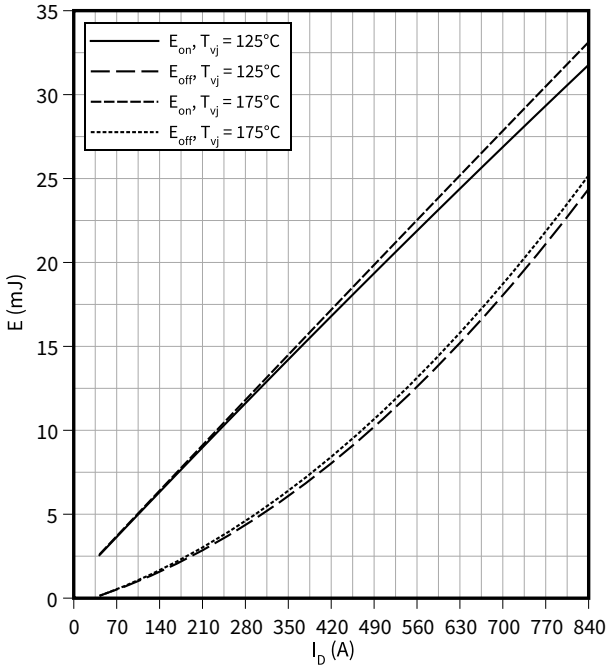
Forward voltage of body diode (typical), MOSFET

$V_{SD} = f(T_{vj})$
$I_{SD} = 420\ A$



Switching losses (typical), MOSFET

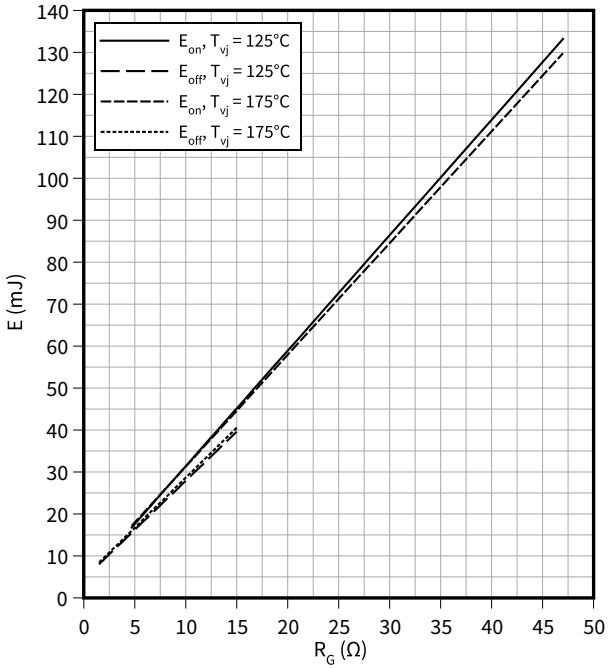
$E = f(I_D)$
$R_{Goff} = 1.5\ \Omega$, $R_{Gon} = 4.7\ \Omega$, $V_{DD} = 600\ V$, $V_{GS} = -3/18\ V$



Switching losses (typical), MOSFET

$E = f(R_G)$

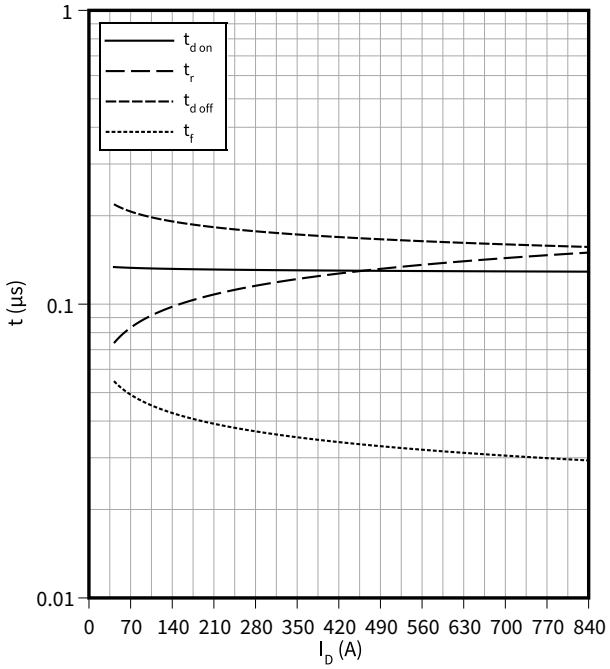
V_{DD} = 600 V, I_D = 420 A, V_{GS} = -3/18 V



Switching times (typical), MOSFET

$t = f(I_D)$

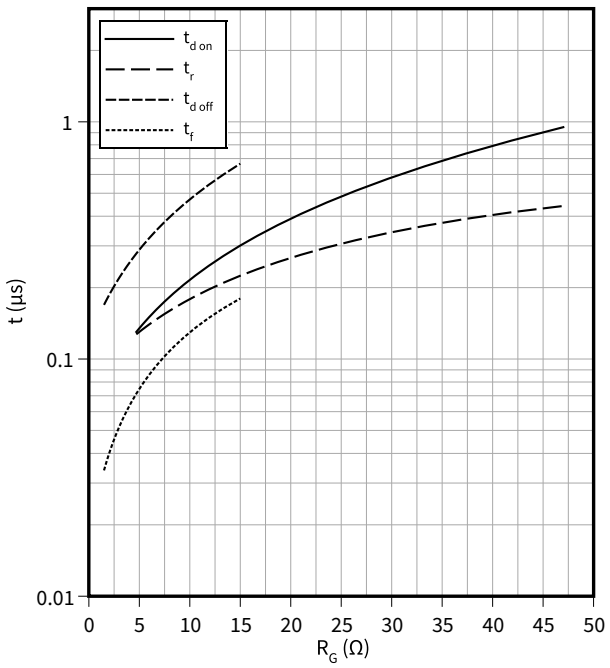
R_{Goff} = 1.5 Ω, R_{Gon} = 4.7 Ω, V_{DD} = 600 V, T_{vj} = 175 °C, V_{GS} = -3/18 V



Switching times (typical), MOSFET

$t = f(R_G)$

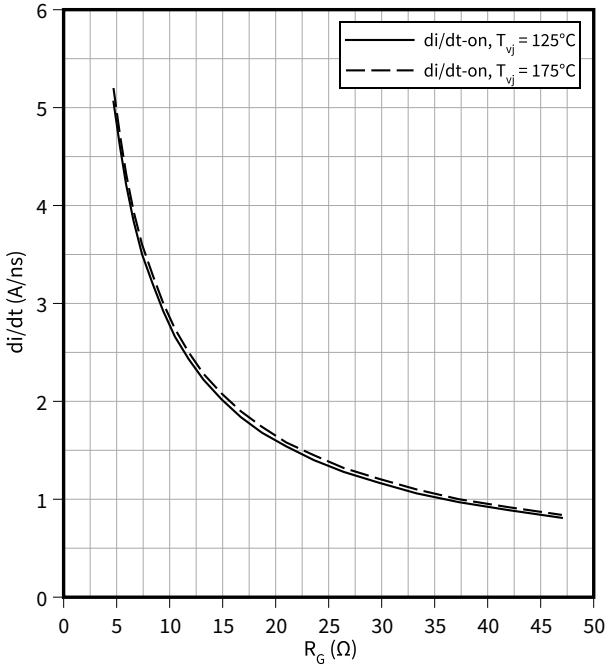
V_{DD} = 600 V, I_D = 420 A, T_{vj} = 175 °C, V_{GS} = -3/18 V



Current slope (typical), MOSFET

$di/dt = f(R_G)$

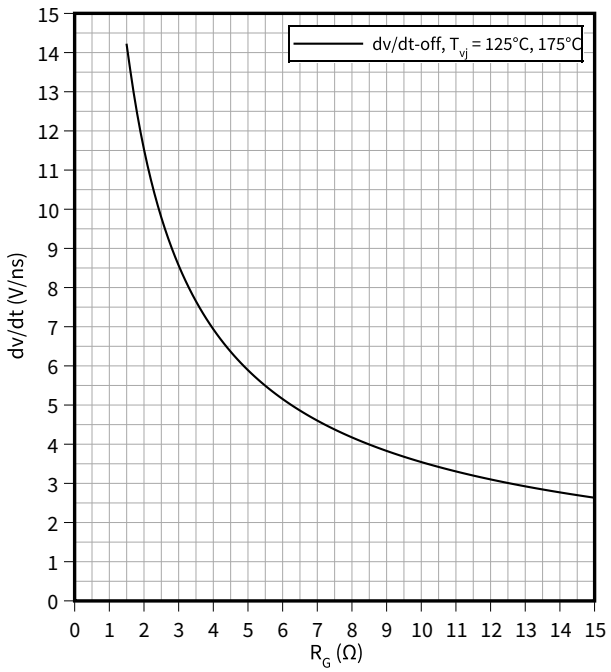
V_{DD} = 600 V, I_D = 420 A, V_{GS} = -3/18 V



Voltage slope (typical), MOSFET

$dv/dt = f(R_G)$

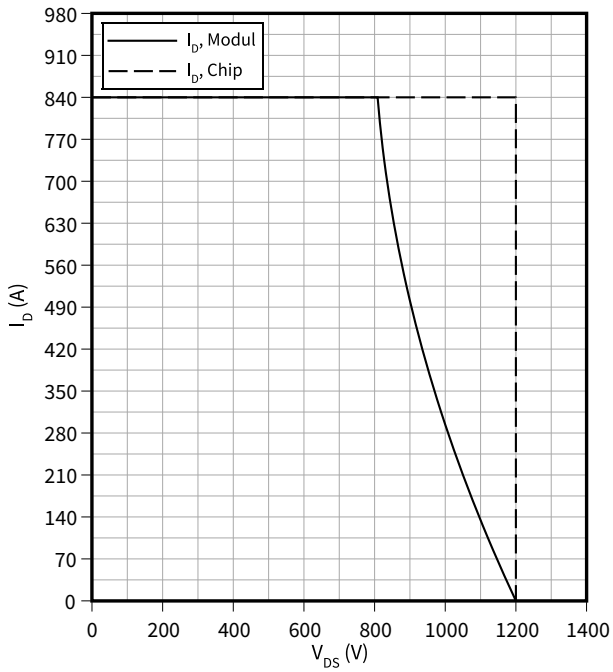
V_{DD} = 600 V, I_D = 420 A, V_{GS} = -3/18 V



Reverse bias safe operating area (RBSOA), MOSFET

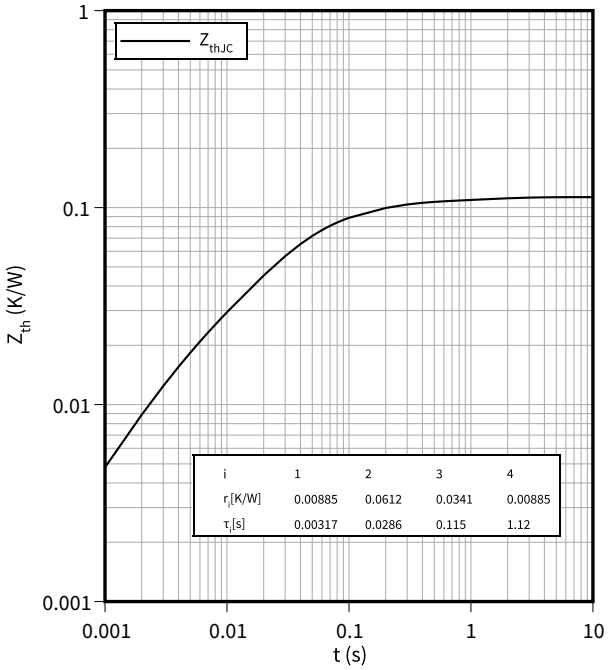
$I_D = f(V_{DS})$

R_{Goff} = 1.5 Ω, T_{vj} = 175 °C, V_{GS} = -3/18 V



Transient thermal impedance , MOSFET

$Z_{th} = f(t)$



5 Circuit diagram

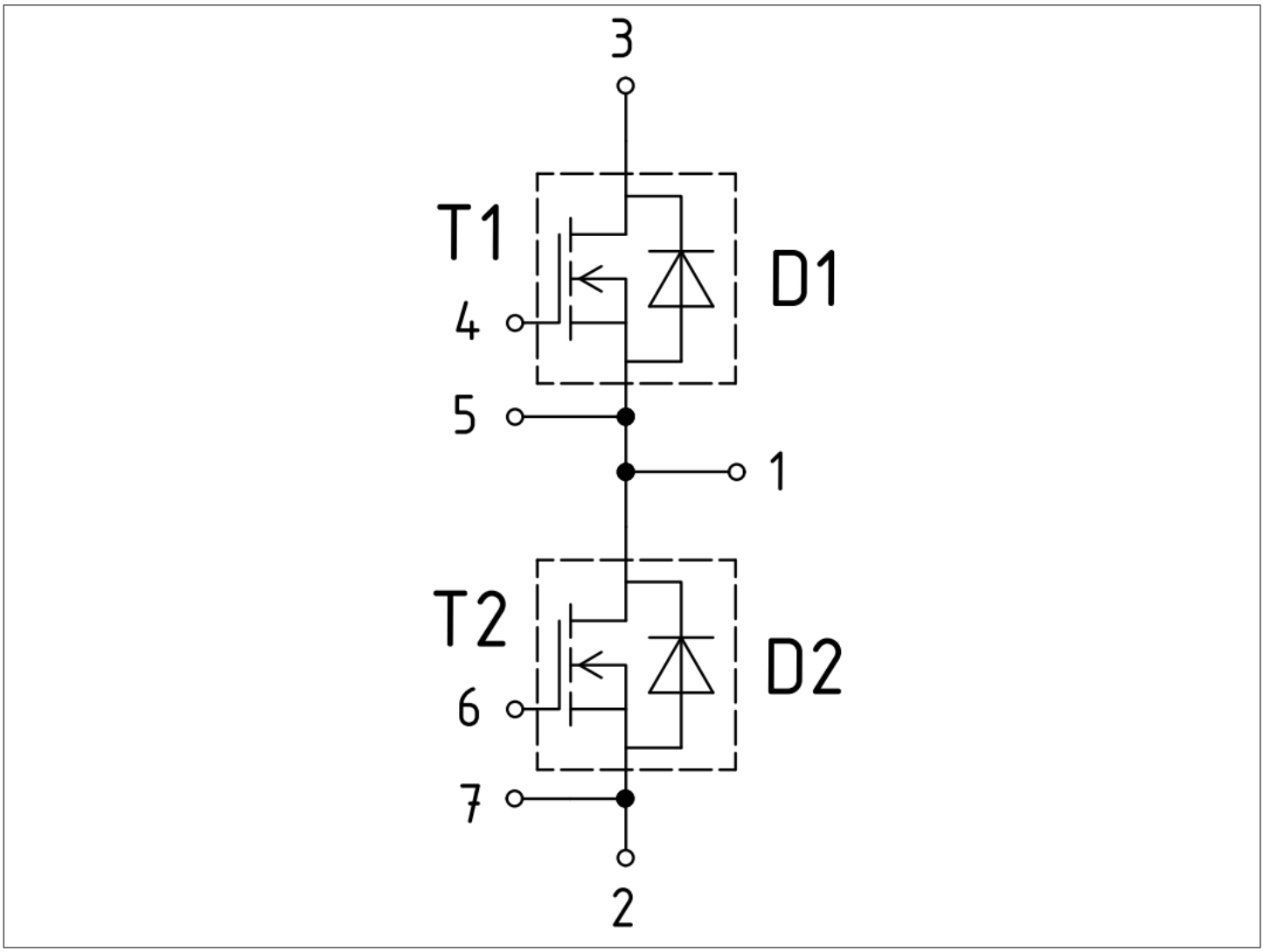


Figure 1

6 Package outlines

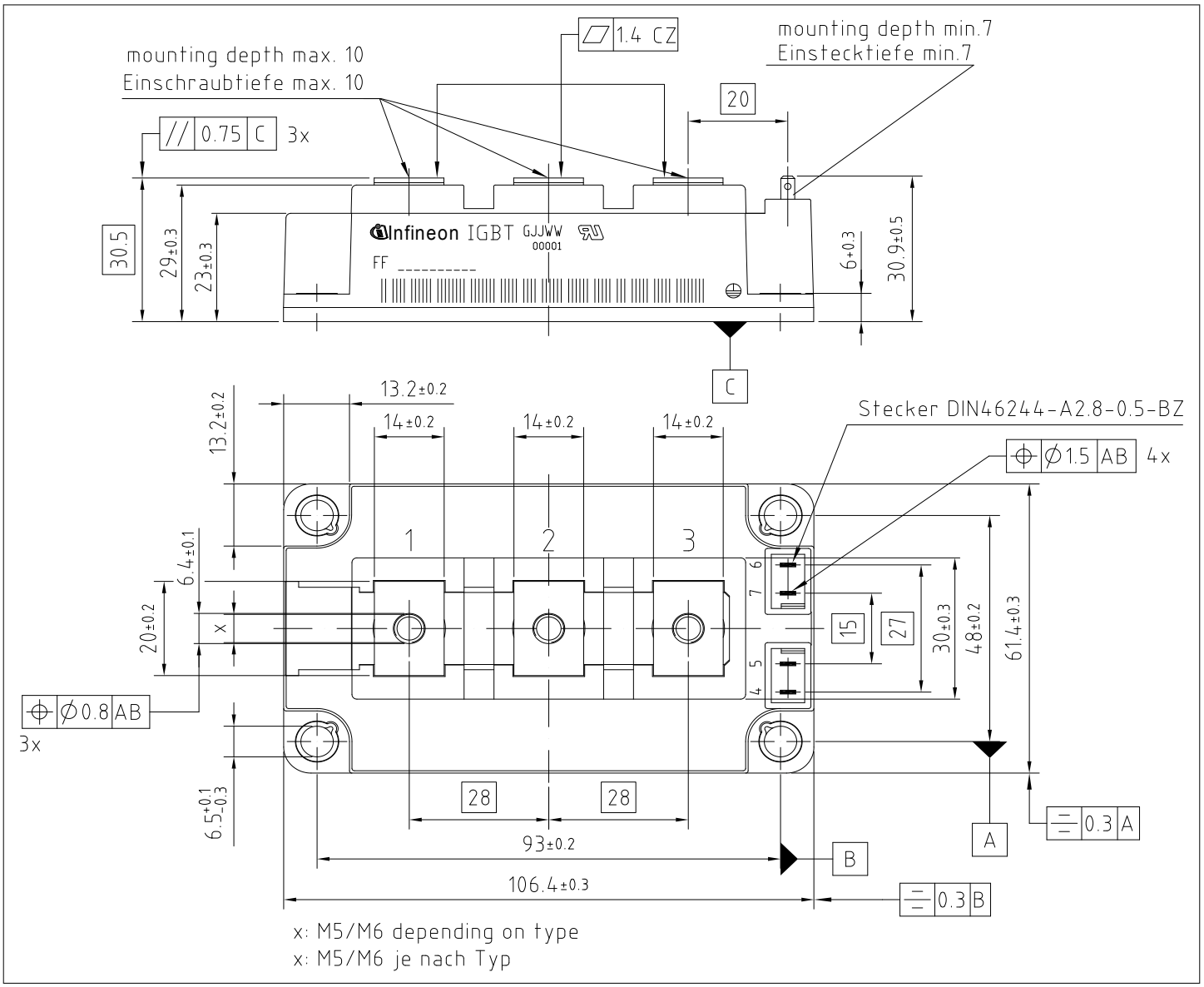


Figure 2

7 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2023-01-20	Initial version
0.20	2023-03-02	Preliminary datasheet

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Edition 2023-03-02

Published by

Infineon Technologies AG

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Document reference
IFX-ABF678-002

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